

C1 end
detecting the endpoint of polishing processing of said film on the basis of a relationship between intensities of the detected reflected lights of the different wavelengths.

C2
2. (amended) A method of detecting an endpoint of polishing processing according to claim 1, wherein said endpoint of polishing processing is detected on the basis of an intensity ratio of said detected reflected lights of different wavelengths.

C3
9. (twice amended) A method of manufacturing a semiconductor device, comprising the steps of:
forming an insulating film on a surface of a wafer;
attaching the wafer having the insulating film formed on its surface to a polishing processing machine;
starting polishing processing of the wafer attached to the polishing processing machine;
simultaneously irradiating onto the surface of said wafer under polishing processing lights having different wavelengths from one another;
detecting respective reflected lights of different wavelengths from the insulating film on said wafer surface generated by the irradiation with the lights of the different wavelengths;
detecting an endpoint of polishing processing on the film by comparing at least an intensity of the detected reflected lights of the different wavelengths;
stopping polishing processing of said wafer on which the endpoint is detected;
detaching the wafer whose polishing processing is stopped from said polishing processing machine; and
forming a new wiring pattern on said insulating film of the wafer detached from said polishing processing machine.

C4
10. (amended) A method of manufacturing a semiconductor device according to claim 9, wherein a polishing rate of the film is evaluated on the basis of the intensities of said detected reflected lights of the different wavelengths so as to change dressing conditions of a dresser to a pad used for polishing processing on the basis of the evaluation result.

Please cancel claims 12-17 without prejudice or disclaimer of the subject matter thereof.

Please amend claims 18-20 and 24 as follows:

18. (amended) A method of detecting an endpoint of polishing processing according to claim 1, wherein a white light provides the lights of the different wavelengths.

C5
19. (amended) A method of detecting an endpoint of polishing processing according to claim 1, wherein in the step of detecting the endpoint, the endpoint is detected on the basis of a spectral intensity of the detected reflected lights of the different wavelengths.

20. (amended) A method of detecting an endpoint of polishing processing according to claim 1, wherein a UV light provides the lights of the different wavelengths.

C6
24. (amended) A method of manufacturing a semiconductor device according to claim 9, wherein the detecting an endpoint of polishing processing on the film by comparing at least an intensity of the detected reflected lights of the

C 6 en91 different wavelengths includes detecting on the basis of a relationship between intensities of the detected reflected lights of the different wavelengths.

Please cancel claim 25 without prejudice or disclaimer of the subject matter thereof.

Please amend claims 26-28 as follows:

C 1 26. (amended) A method of manufacturing a semiconductor device according to claim 9, wherein the detecting an endpoint of polishing processing is detected on the basis of an intensity ratio of the detected reflected lights of different wavelengths.

27. (amended) A method of manufacturing a semiconductor device according to claim 9, wherein a white light provides the lights of the different wavelengths.

28. (amended) A method of manufacturing a semiconductor device according to claim 9, wherein a UV light provides the lights of the different wavelengths.

REMARKS

Applicants note that claims 5, 6 and 20-23 stand withdrawn from consideration.

By the present amendment, independent claims 1 and 9 have been amended to clarify the features of the present invention, with claims 12-17 and 25 being canceled and the other claims amended to depend appropriately from independent claims 1 and 9.